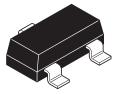
### **30V P-CHANNEL ENHANCEMENT MODE MOSFET**

**SUMMARY** 

 $V_{(BR)DSS} = -30V$ ;  $R_{DS(ON)} = 0.21\Omega$ ;  $I_D = -1.6A$ 

#### **DESCRIPTION**

This new generation of trench MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.



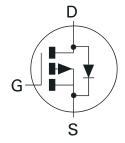
SOT23

#### **FEATURES**

- Low on-resistance
- · Fast switching speed
- · Low threshold
- Low gate drive
- SOT23 package

#### **APPLICATIONS**

- DC DC converters
- Power management functions
- Disconnect switches
- Motor control



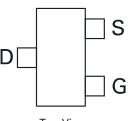
### ORDERING INFORMATION

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXMP3A13FTA	7″	8mm	3000 units
ZXMP3A13FTC	13"	8mm	10000 units

### **DEVICE MARKING**

• 313





Top View



### **ABSOLUTE MAXIMUM RATINGS**

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V <sub>DSS</sub>	-30	V
Gate Source Voltage	V <sub>GS</sub>	±20	V
Continuous Drain Current $V_{GS}$ =10V; $T_A$ =25°C (b) $V_{GS}$ =10V; $T_A$ =70°C (b) $V_{GS}$ =10V; $T_A$ =25°C (a)	I <sub>D</sub>	-1.6 -1.3 -1.4	А
Pulsed Drain Current (c)	I <sub>DM</sub>	-6	А
Continuous Source Current (Body Diode) (b)	I <sub>S</sub>	-1.2	А
Pulsed Source Current (Body Diode) (c)	I <sub>SM</sub>	-6	А
Power Dissipation at T <sub>A</sub> =25°C (a) Linear Derating Factor	$P_{D}$	625 5	mW mW/°C
Power Dissipation at T <sub>A</sub> =25°C (b) Linear Derating Factor	P <sub>D</sub>	806 6.4	mW mW/°C
Operating and Storage Temperature Range	T <sub>j</sub> :T <sub>stg</sub>	-55 to +150	°C

#### THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to ambient (a)	$R_{\theta JA}$	200	°C/W
Junction to ambient (b)	$R_{\theta JA}$	155	°C/W

#### NOTES

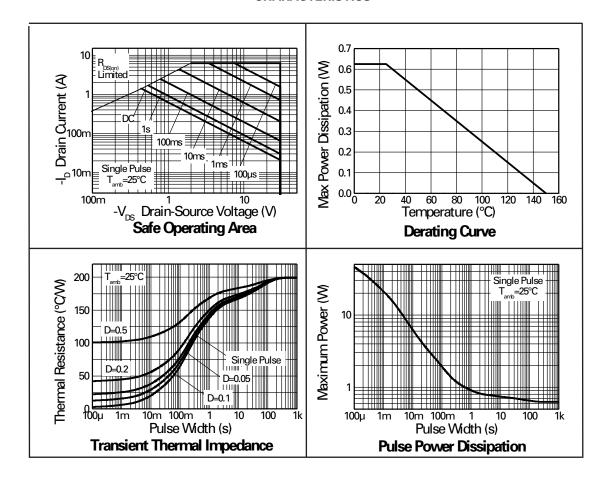


 $<sup>(</sup>a) For a device surface mounted on 25 mm\ x\ 25 mm\ FR4\ PCB\ with\ high\ coverage\ of\ single\ sided\ 1oz\ copper,\ in\ still\ air\ conditions$ 

<sup>(</sup>b) For a device surface mounted on FR4 PCB measured at t≤5 secs.

<sup>(</sup>c) Repetitive rating 25mm  $\times$  25mm FR4 PCB, D = 0.05, pulse width  $10\mu s$  - pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.

### **CHARACTERISTICS**



SEMICONDUCTORS

# **ELECTRICAL CHARACTERISTICS** (at $T_A = 25^{\circ}C$ unless otherwise stated)

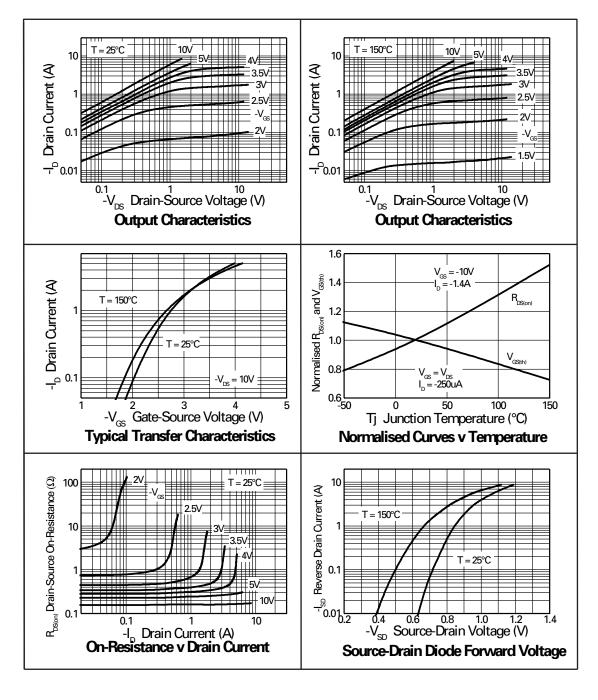
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS		
STATIC								
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	-30			V	I <sub>D</sub> =-250μA, V <sub>GS</sub> =0V		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>			-0.5	μΑ	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V		
Gate-Body Leakage	I <sub>GSS</sub>			100	nA	$V_{GS}$ = $\pm 20V$ , $V_{DS}$ = $0V$		
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	-1.0			V	I <sub>D</sub> =-250μA, V <sub>DS</sub> = V <sub>GS</sub>		
Static Drain-Source On-State Resistance (1)	R <sub>DS(on)</sub>			0.210 0.330	Ω	V <sub>GS</sub> =-10V, I <sub>D</sub> =-1.4A V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-1.1A		
Forward Transconductance (1)(3)	g <sub>fs</sub>		2.4		S	V <sub>DS</sub> =-15V,I <sub>D</sub> =-1.4A		
DYNAMIC (3)	•	•						
Input Capacitance	C <sub>iss</sub>		206		pF			
Output Capacitance	Coss		59.3		pF	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, f=1MHz		
Reverse Transfer Capacitance	C <sub>rss</sub>		49.2		pF			
SWITCHING(2) (3)								
Turn-On Delay Time	t <sub>d(on)</sub>		1.5		ns			
Rise Time	t <sub>r</sub>		3.0		ns	V <sub>DD</sub> =-15V, I <sub>D</sub> =-1A		
Turn-Off Delay Time	t <sub>d(off)</sub>		11.1		ns	$R_{G}=6.0\Omega$ , $V_{GS}=-10V$		
Fall Time	t <sub>f</sub>		7.6		ns			
Gate Charge	Qg		3.8		nC	V <sub>DS</sub> =-15V,V <sub>GS</sub> =-5V, I <sub>D</sub> =-1.4A		
Total Gate Charge	Qg		6.4		nC			
Gate-Source Charge	$Q_{gs}$		0.69		nC	V <sub>DS</sub> =-15V,V <sub>GS</sub> =-10V, I <sub>D</sub> =-1.4A		
Gate-Drain Charge	$Q_{gd}$		2.0		nC			
SOURCE-DRAIN DIODE					,			
Diode Forward Voltage (1)	V <sub>SD</sub>		-0.85	-0.95	V	T <sub>J</sub> =25°C, I <sub>S</sub> =-1.1A, V <sub>GS</sub> =0V		
Reverse Recovery Time (3)	t <sub>rr</sub>		15.6		ns	T <sub>J</sub> =25°C, I <sub>F</sub> =-0.95A,		
Reverse Recovery Charge (3)	Q <sub>rr</sub>		9.6		nC	di/dt= 100A/μs		

### NOTES:

- (1) Measured under pulsed conditions. Width=300 $\mu s.$  Duty cycle  $\leq~2\%$  .
- (2) Switching characteristics are independent of operating junction temperature.
- (3) For design aid only, not subject to production testing.

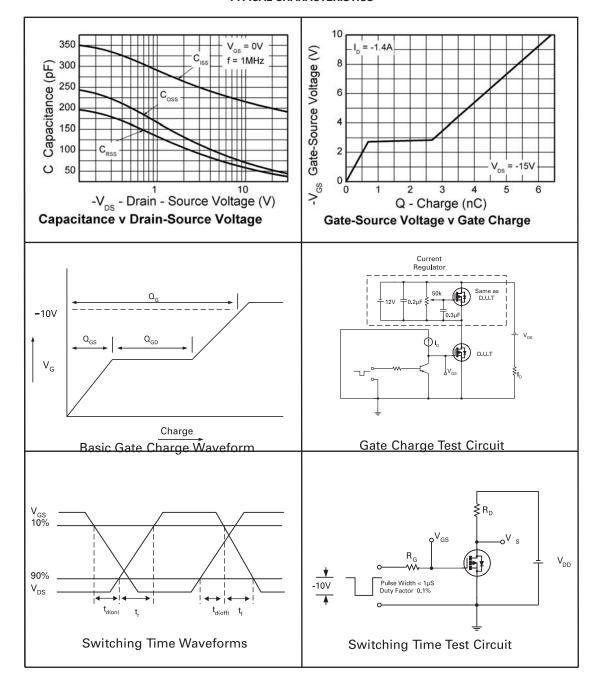


#### **TYPICAL CHARACTERISTICS**





#### **TYPICAL CHARACTERISTICS**





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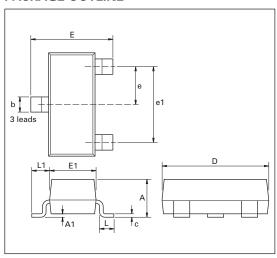
- "Preview"Future device intended for production at some point. Samples may be available
- "Active"Product status recommended for new designs
- "Last time buy (LTB)"Device will be discontinued and last time buy period and delivery is in effect
- "Not recommended for new designs"Device is still in production to support existing designs and production
- "Obsolete"Production has been discontinued

Datasheet status key:

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### **PACKAGE OUTLINE**



#### **PACKAGE DIMENSIONS**

DIM	Millimeters		Inches			Millimeters		Inches	
	Min	Max	Min	Max	DIM	Min	Max	Min	Max
Α	-	1.12	-	0.044	e1	1.90 NOM		0.075 NOM	
A1	0.01	0.10	0.0004	0.004	Е	2.10	2.64	0.083	0.104
b	0.30	0.50	0.012	0.020	E1	1.20	1.40	0.047	0.055
С	0.085	0.020	0.003	0.008	L	0.25	0.60	0.0098	0.0236
D	2.80	3.04	0.110	0.120	L1	0.45	0.62	0.018	0.024
е	0.95 NOM		0.037	NOM	_	_	_	_	_

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